Time		Coherence	Qubit	Material	Host	Date	Reference	Source	0
20	ms	T_1	HY/e[a]	$^{28}Si/SiGe$	2D	2021-12	1	p4	1
50	μs	T_1	LD/e	GaAs/AlGaAs	2D	2003-11	2	abstract	2
0.85	ms	T_1	LD/e	GaAs/AlGaAs	2D	2004-07	3	p4	3
1	s	T_1	LD/e	GaAs/AlGaAs	2D	2008-01	4	p4 and Fig. 3c the leftmost blue point	4
0.6	s[b]	T_1	LD/e	Si/SiGe	2D	2009-08	5	Fig. 5	5
40	ms	T_1	LD/e	Si/SiO_2	2D	2010-03	6	p4 and Fig. 4 the leftmost red point	6
2.8	s	T_1	LD/e	Si/SiGe	2D	2011-04	7	p3 and Fig. 3	7
1	μs	T_1	LD/e	InAs	1D	2012-10	8	Fig. 4d	8
2.6	s	T_1	LD/e	Si/SiO_2	2D	2013-06	9	p3	9
85	ms	T_1	LD/e	GaAs/AlGaAs	2D	2014-12	10	p2 and Fig. 3	10
3.7	ms	T_1	LD/e	GaAs/AlGaAs	2D	2016-07	11	p3 and Fig. 2	11
0.17	s	T_1	LD/e	Si/SiGe	2D	2016-11	12	Fig. 6	12
10	s	T_1	LD/e	GaAs/AlGaAs	2D	2017-10	13	Fig. 2 the lowest green point	13
50	ms	T_1	LD/e	Si/SiGe	2D	2018-02	14	p1 and ED Fig. 3b	14
0.15	s[c]	T_1	LD/e	$^{28}Si/SiO_2$	2D	2018-08	15	p2 and p4	15
2.8	ms[d]	T_1	LD/e	$^{28}Si/SiO_2$	2D	2018-08	15	p4 and Fig. 3a	16
1	s	T_1	LD/e	$^{28}Si/SiO_2$	2D	2018-10	16	p2	17
57	s	T_1	LD/e	GaAs/AlGaAs	2D	2018-12	17	p3 and Fig. 4a	18
0.16	s[e]	T_1	LD/e	Si/SiGe	2D	2019-04	18	Fig. 2	19
5	s[f]	T_1	LD/e	Si/SiGe	2D	2019-04	18	p4	20
1.5	ms	T_1	LD/e	GaAs/AlGaAs	2D	2019-06	19	Fig. 2	21
0.13	s	T_1	LD/e	$^{28}Si/SiGe$	2D	2019-12	20	p4	22
1	s	T_1	LD/e	$^{28}Si/SiGe$	2D	2020-03	21	p6 and Fig. 4a	23
3.7	ms	T_1	LD/e[g]	$^{28}Si/SiO_2$	2D	2020-04	22	p2	24
90	ms	T_1	LD/e	Si/SiO_2	2D	2020-06	23	Fig. 1c	25
9	s	T_1	LD/e	Si/SiO_2	1D	2021-03	24	p3 and Fig. 3a the leftmost blue point	26
1.3	ms	T_1	LD/e	Si/SiGe	2D	2021-06	25	p1 for Q3	27
10	ms	T_1	LD/e	Si/SiO_2	1D	2021-09	26	p2 and Fig. 2a	28
1.6	s	T_1	LD/e	$^{28}Si/SiO_2$	2D	2022-03	27	p4 and Fig. 3c	29
5	ns	T_1	LD/h	GaAs/AlGaAs	1D	2016-12	28	p4 and SM pS5	30
86	μs	T_1	LD/h	Ge/Si	1D	2018-11	29	p3 and Fig. 3c the leftmost point	31
60	μs	T_1	LD/h	GaAs/AlGaAs	2D	2019-12	30	abstract and Fig. 4	32
9	μs	T_1	LD/h	Ge/SiGe	2D	2020-01	31	p3 and Fig. 2f	33
32	ms	T_1	LD/h	Ge/SiGe	2D	2020-08	32	p3	34
1.2	ms	T_1	LD/h	Ge/SiGe	2D	2020-12	33	p4 and Fig. 3a	35
16	ms	T_1	LD/h	Ge/SiGe	2D	2021-03	34	Fig. S5 dot 3	36
3	ms[h]	T_1	LD/h	BLG	2D	2021-12	35	p5	37
3.7	μs	T_1	LD/h	Ge/Si	1D	2022-12	36	SM p13 and SFig. 7.1d	38
6	s	T_1	LD/i	Si:P	imp	2010-10	37	p2	39
0.7	s	T_1	LD/i	Si:P	imp	2012-09	38	p3	40
1.8	s	T_1	LD/i	Si:P	imp	2013-10	39	Fig. 3	41
1.3	s	T_1	LD/i[i]	$^{28}Si:P$	imp	2016-10	40	p4	42
3	s	T_1	LD/i	$^{28}Si:P$	imp	2016-10	41	p3	43
30	s	T_1	LD/i	Si:P	imp	2017-03	42	Fig. 2b the lowest point	44
1.3	s	T_1	LD/i	Si:P	imp	2018-12	43	p3 and Fig. 2b	45
9.3	s	T_1	LD/i	Si:P	imp	2018-12	44	p3 and Fig. 1f	46
4.2	s	T_1	LD/i	Si:P	imp	2019-02	45	p3	47
9.8	s	T_1	LD/i	Si:P	imp	2019-05	46	Fig. 2c	48
5	ms	T_1	LD/i	$^{28}Si:B$	imp	2021-01	47	p3 and Fig. 3b	49
3.4	s	T_1	LD/i	$^{28}Si:P$	imp	2021-12	48	p6 and SFig. 3c	50

TABLE I-1. Spin coherence times (part 1). Superscripts stand for the following. [a]: EO qubit. [b]: *(estimated)* Fig. 5 the lowest point. [c]: At 0.1 kelvin. [d]: At 1.1 kelvin. [e]: With micromagnet. [f]: No micromagnet. [g]: At 1 kelvin. [h]: The reference states "...the relaxation time is on the order of milliseconds". We use 3 ms as a representative value, as it corresponds to the "load phase" in the measurement cycle. [i]: Qubit defined in the rotating frame.

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